



Micro-311

Microfabrication of
Flexible and Stretchable
Neuroelectronic interfaces

Giuseppe Schiavone
Neuro-X Institute

Microfabrication of Flexible and Stretchable Neuroelectronic interfaces

- Overview
- Silicon-based neurotechnology
- Flexible neurotechnology
- Stretchable neurotechnology

Why Flexible (or beyond → stretchable) Electronics?

- Mechanical / geometrical requirements from specific applications:
→ System must be able to withstand bending and deformation without failing
- Some applications driving the development of flexible electronics:

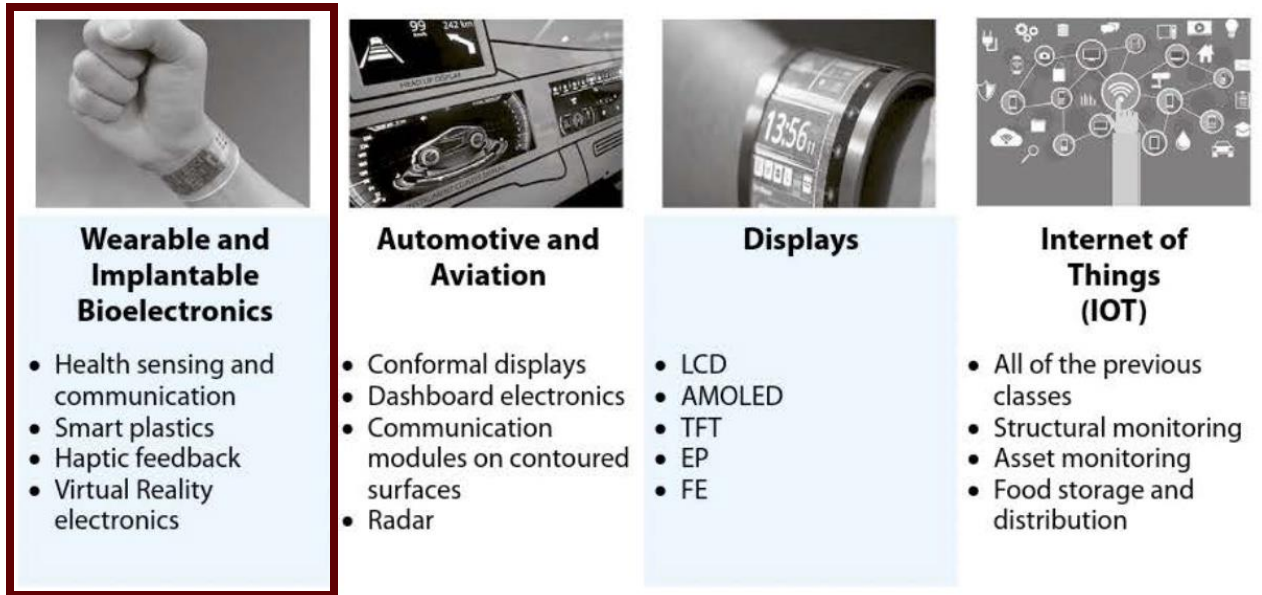


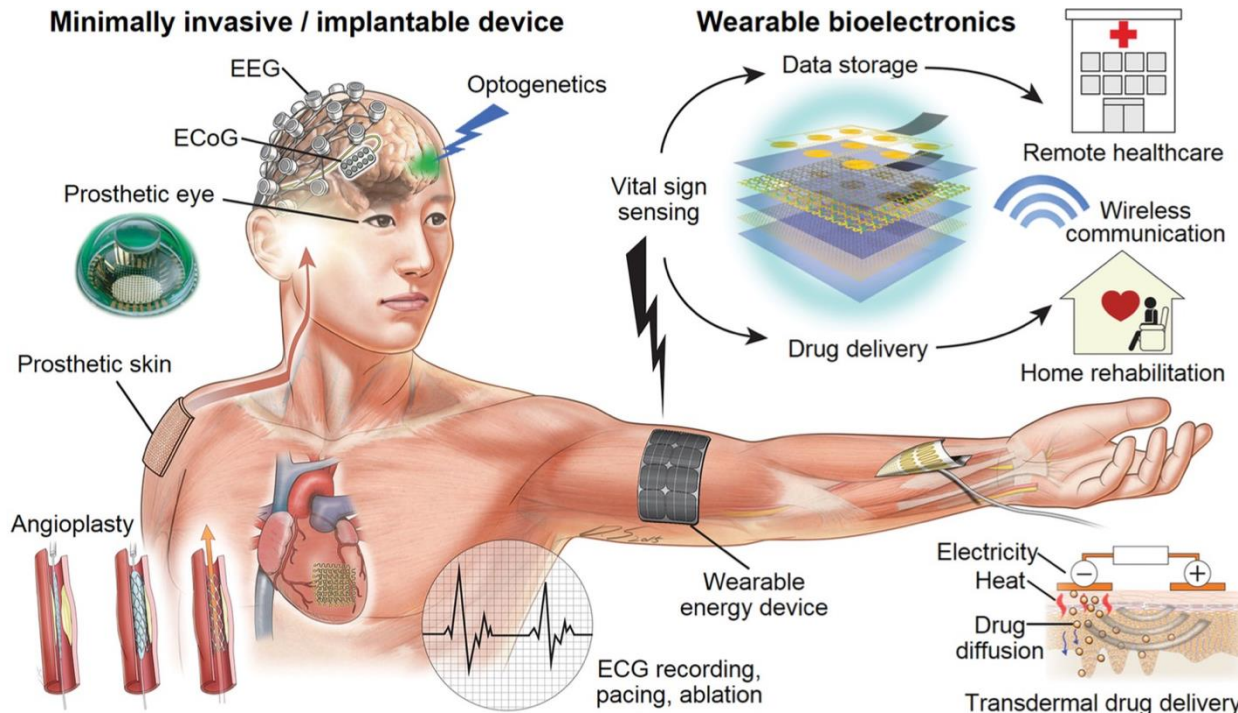
FIGURE 21.1 Applications of flexible electronic systems.

EPFL *Wearables and Implantables*

- **Wearables.** Flexible electronic systems that can be worn by a consumer as an accessory or as a part of clothing. (In reality: can also be non electronic, can be applied to skin or other non-planar surface, can have a medical purpose.)

Choi *et al.*, 2016, *Advanced Materials*

- **Implantables.** A device that is deployed internally in the human (or animal) body.



A geometrical and mechanical challenge

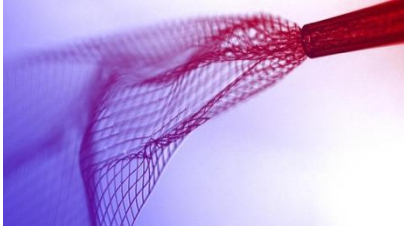
Complex topologies



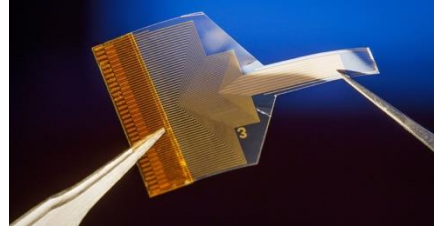
Mobile bodies



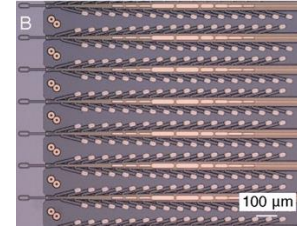
- Neurotechnology must **conform** curvilinear and mobile bodies
- **Elasticity** is needed to follow the body movement and deformation



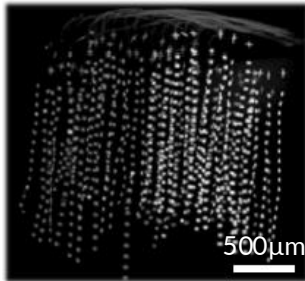
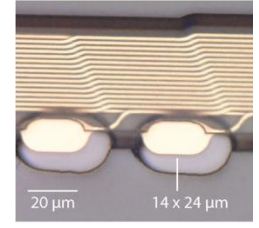
Nanomesh
Jia Liu - Harvard



Transparent ECoG
D Kuzum- UCSD



Neuralink



NET 1'024 electrodes
L. Luan, Rice Univ.

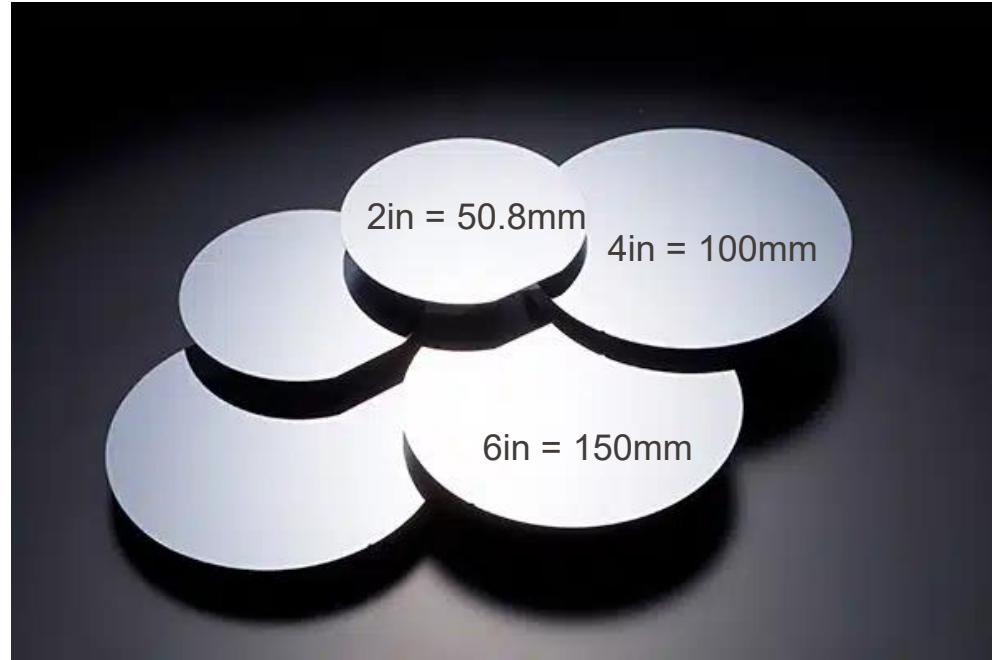


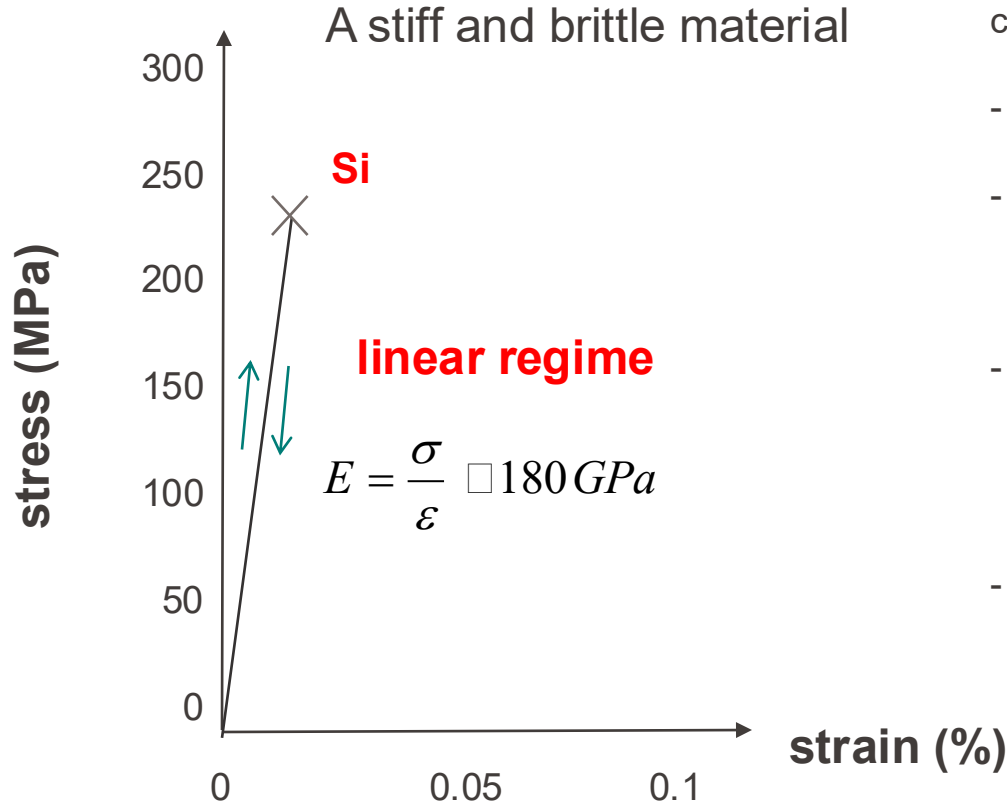
graphene electrodes
InBrain - Spain



Soft ECoG – EPFL / Neurosoft Bioelectronics

- diameter: 2in – 12in
- *12in: modern semicond. fab.*
- thickness: 275 - 1'000 μm
- flatness
- orientation flat and notch
- *(100) or (111) orientation*
(anisotropy in some properties)





“Inherited” from μ -electronics because of the CMOS capabilities

- Excellent control over the mechanical properties.
- **Thermal stability:** High melting point and good thermal conductivity make it robust through high-temperature steps (oxidation, diffusion, anneals).
- **Surface chemistry control:** Surfaces can be precisely cleaned, passivated, and functionalized; Si/SiO₂/Si₃N₄ stacks are well understood for adhesion and protection.
- **Scale & cost:** Abundant material, mature equipment and supply-chain. Decades of CMOS know-how transfer directly to MEMS.

Silicon-based neurotechnology

1D

- Planar 2D structural design
- 1D sites spatial coverage
- Example: Michigan Probe

Michigan Probe, 1985

1.5D

- Planar 2D design
- 1.5D sites spatial coverage
- Example: Neuropixel (IMEC Probe)

Neuropixel Probe, 2017

2D

- Out-of-Plane 3D structural design
- 2D sites spatial coverage
- Example: Utah Electrode Array

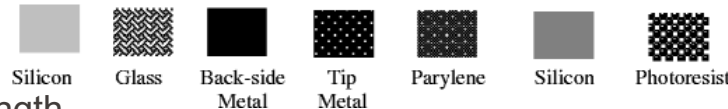
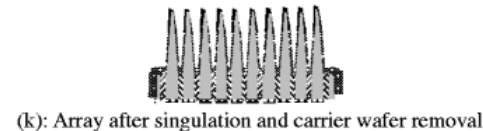
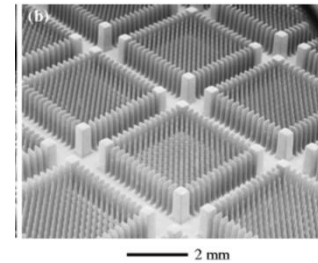
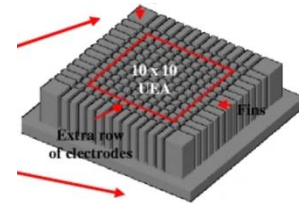
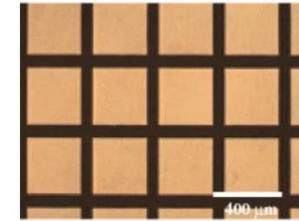
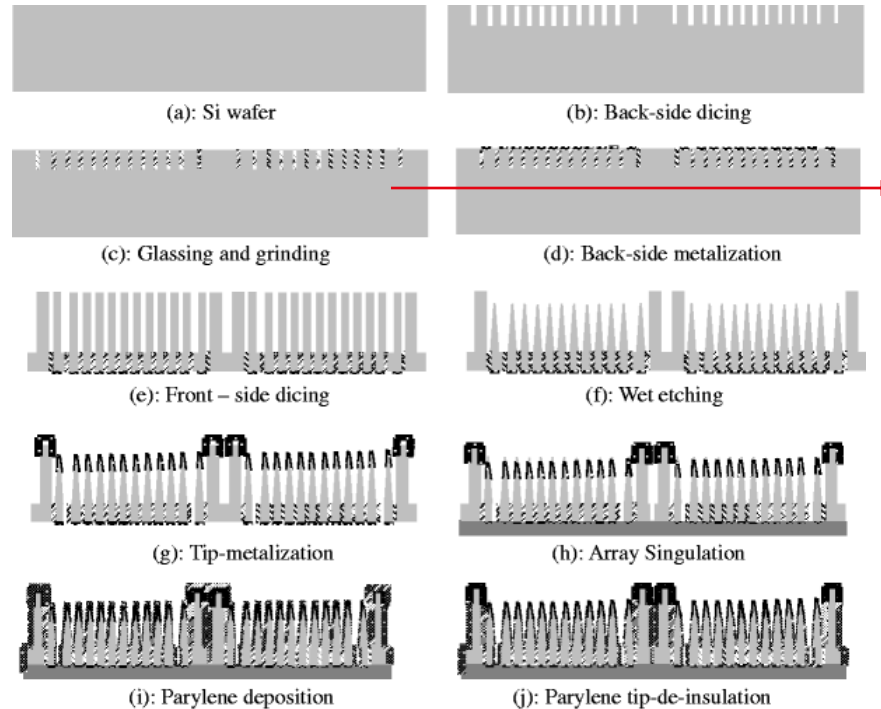
Utah Electrode Array, 1991

3D

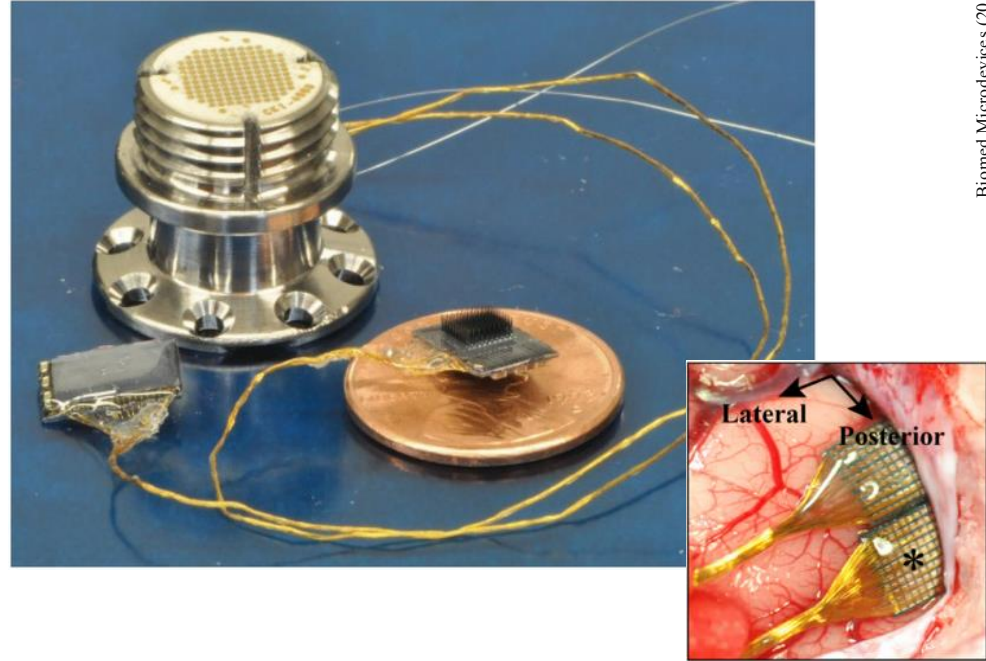
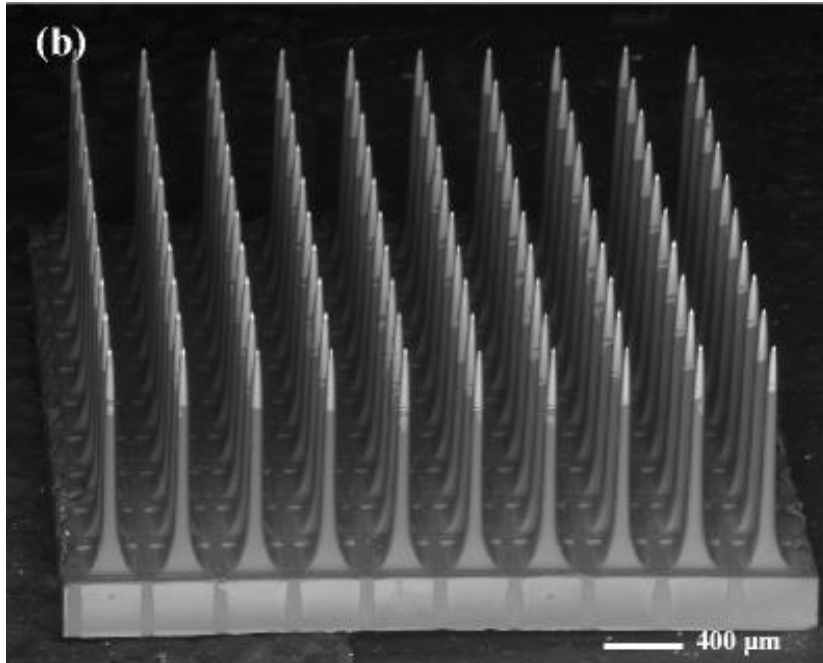
- Out-of-Plane 3D structural design
- 3D sites spatial coverage
- Example: Michigan 3D Array

Michigan 3D Array, 1991

- a. **Backside dicing**
→ 10x10 0.5mm deep matrix
- b. **Glassing**
- c. **Grinding**
- d. **Back-side metallization**
→ Pt/TiW/Pt sputtering
- e. **Front-side dicing**
→ 1.5mm deep columns
- f. **Wet etching**
→ HF:HNO₃ (1:19 ratio)
- g. **Tip metallization**
→ sputtered Ti/Ir then lift-off
- i. **Parylene deposition**
→ LPCVD, 3μm thick
- j. **De-insulation**
→ oxygen plasma etching, 30-350μm length



The Utah array

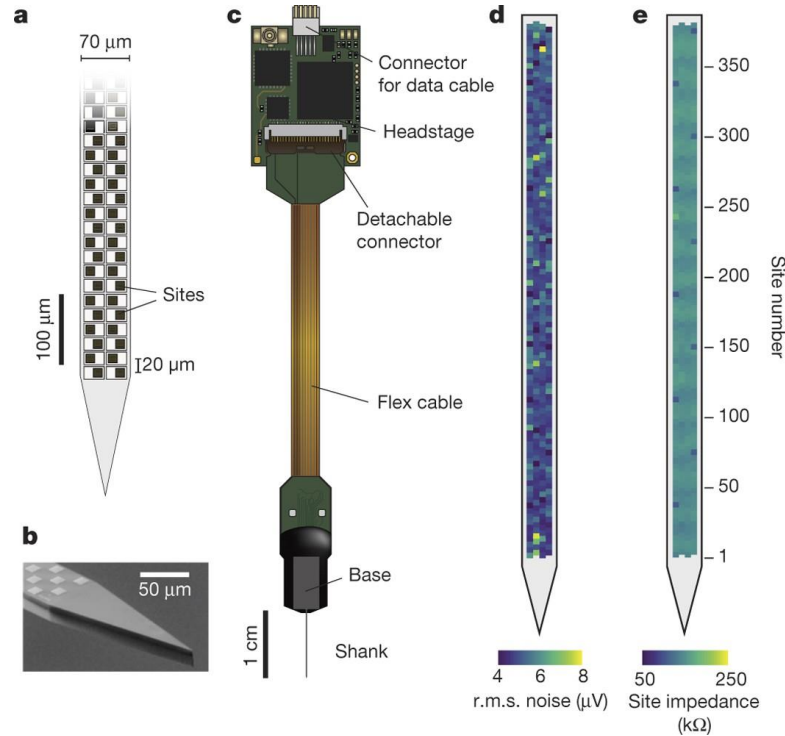


Xianzong Xie *et al* 2014 *J. Neural Eng.* 11 026016

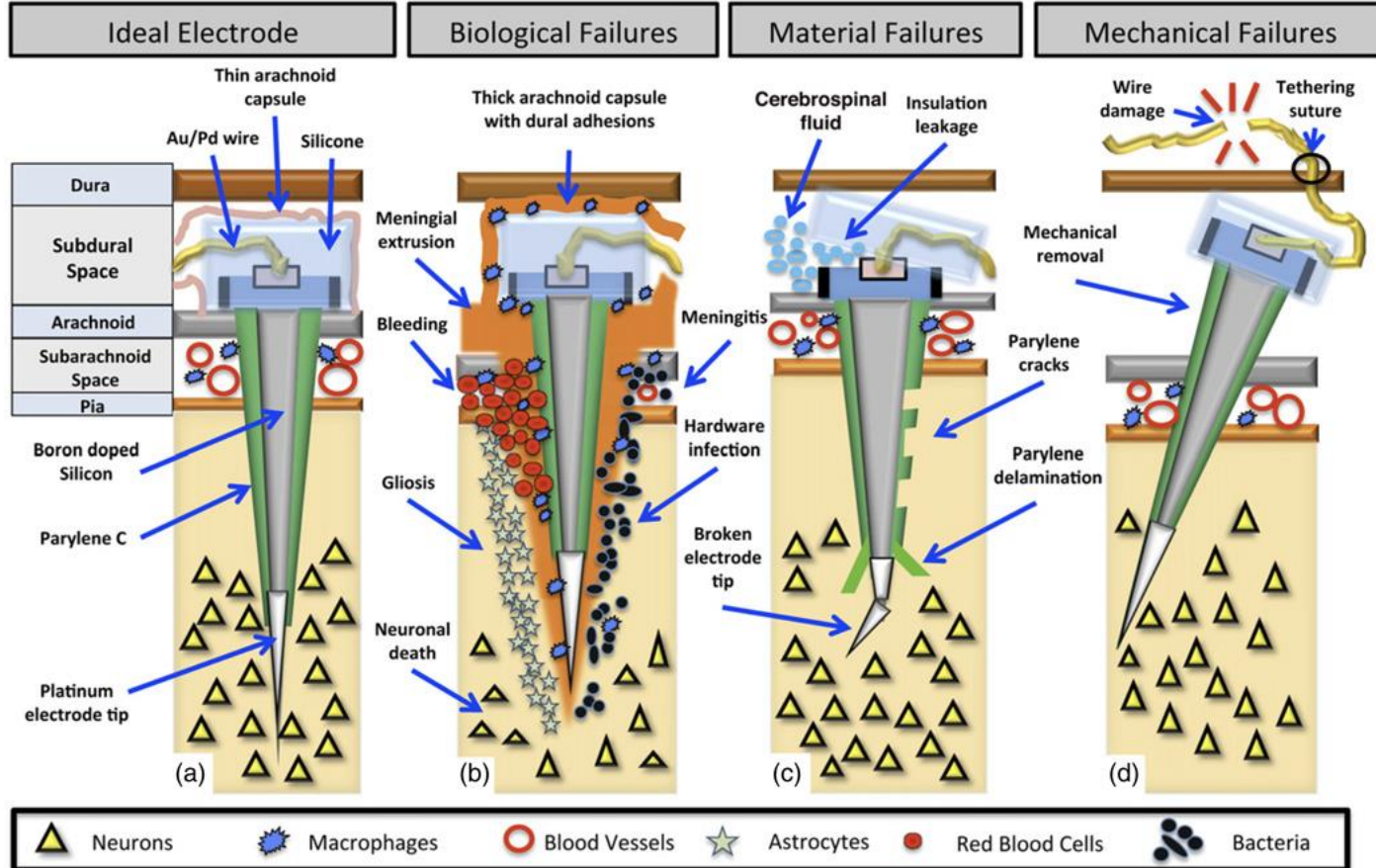


The Neuropixel: Active silicon probe

User-programmable switches that allow the recording channels to address 384 of the **960 total sites** simultaneously
 130nm CMOS technology



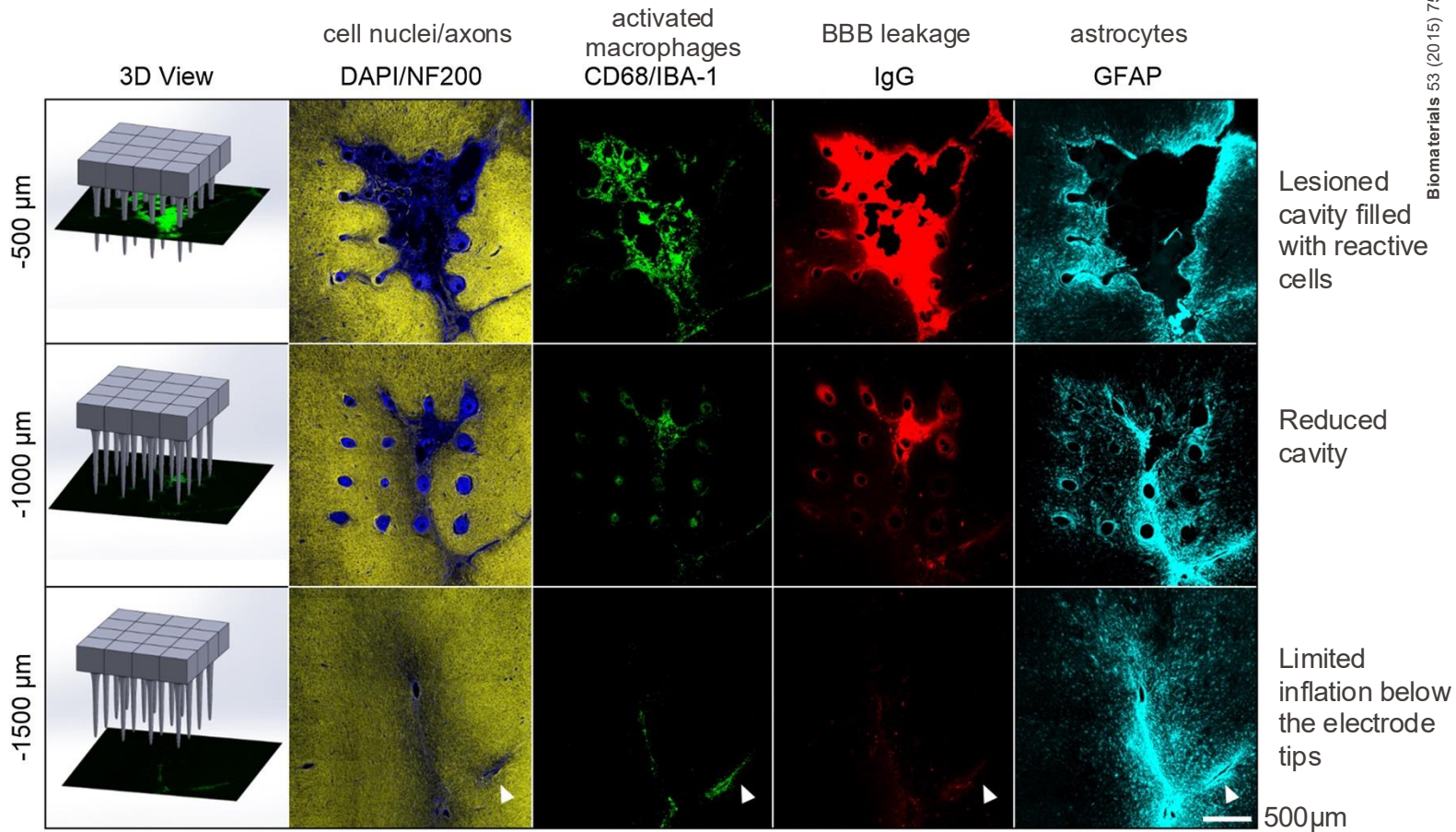
Damage to implant



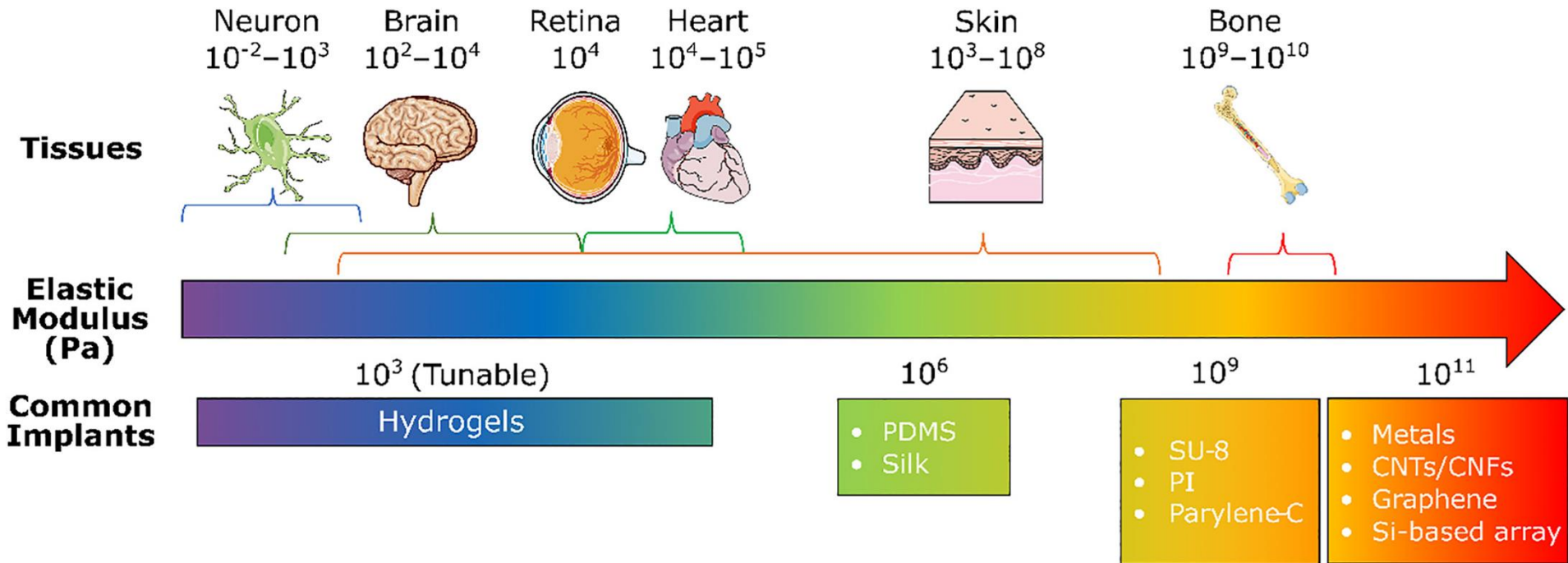
Damage to brain tissue

4x4 Si shanks,
1mm long,
400 μ m apart
1.2x1.2 mm²

Timepoint: 4w



Man-made vs biological materials



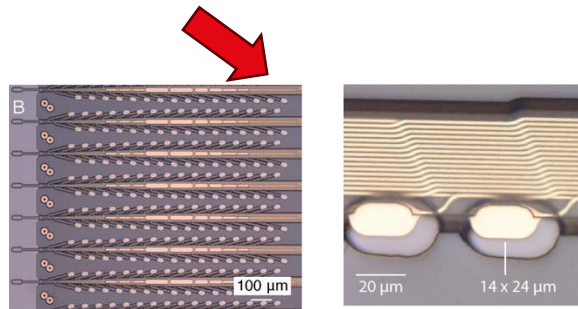
Flexible neural interfaces

- Planar 2D structural design
- 1D sites spatial coverage
- Example: Michigan Probe

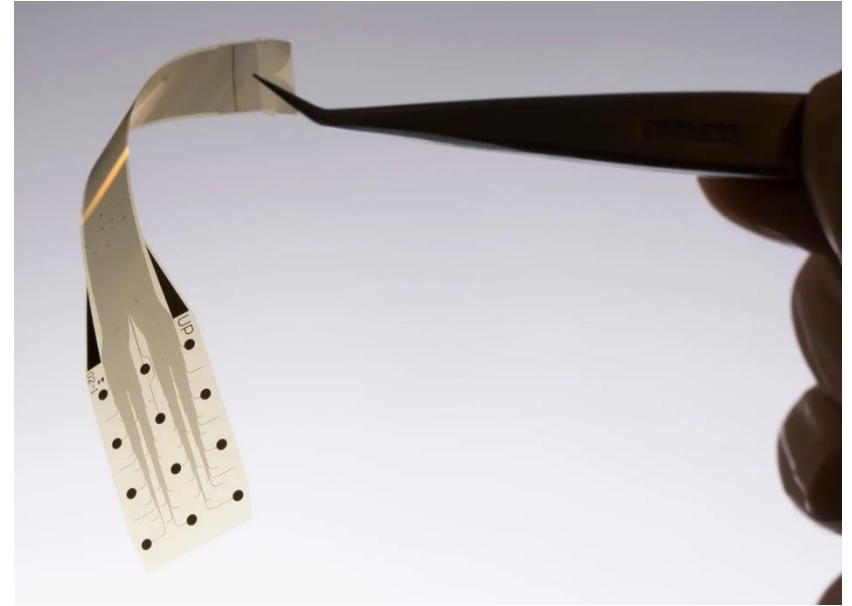
- Planar 2D design
- 1.5D sites spatial coverage
- Example: Neuropixel (IMEC Probe)

- Out-of-Plane 3D structural design
- 2D sites spatial coverage
- Example: Utah Electrode Array

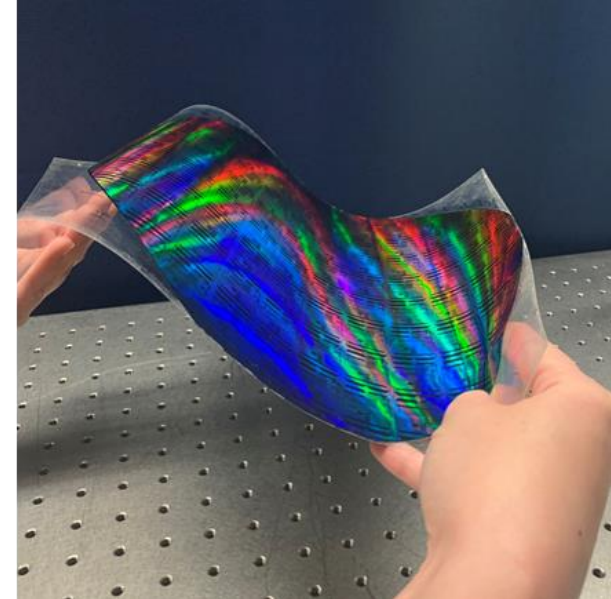
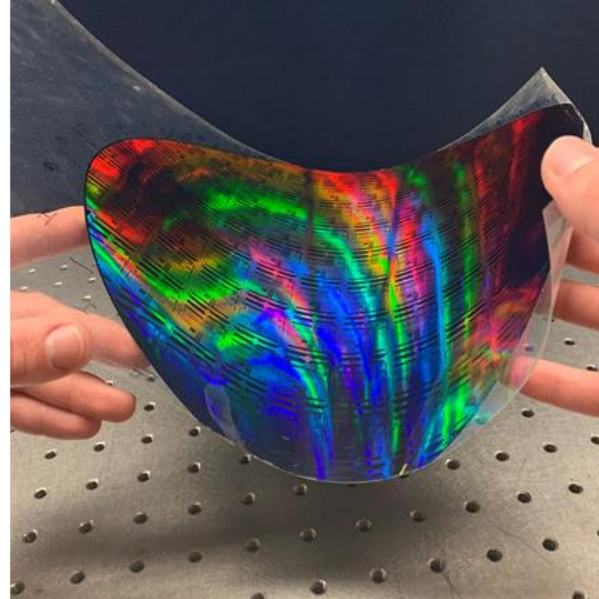
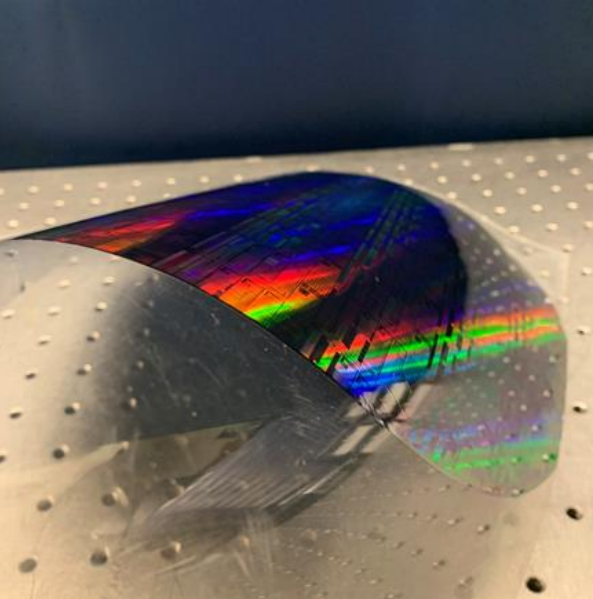
- Out-of-Plane 3D structural design
- 3D sites spatial coverage
- Example: Michigan 3D Array



Neuralink



Graphene electrodes
InBrain - Spain



<https://doi.org/10.1038/s41598-024-61055-w>

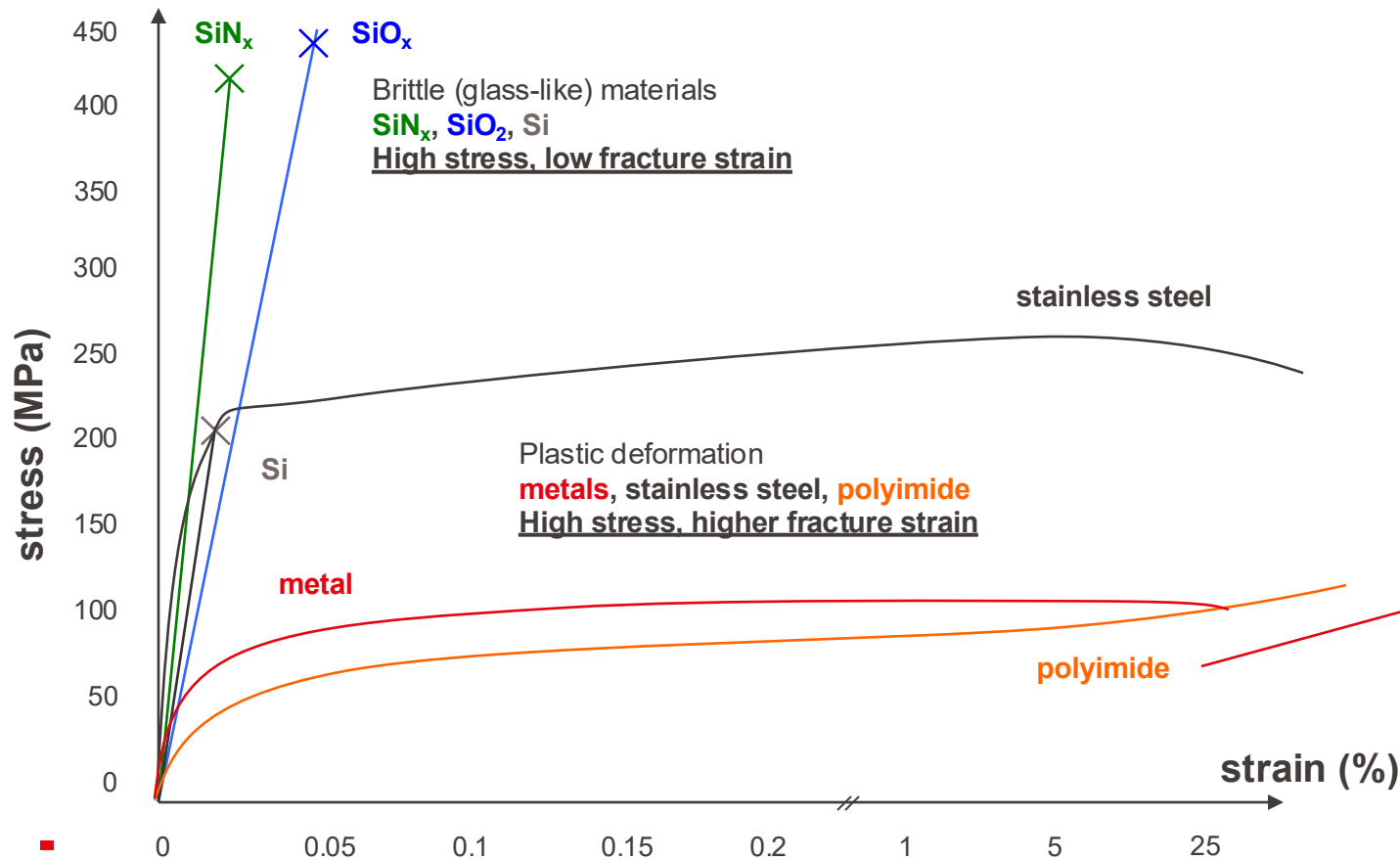
Flexural rigidity formula

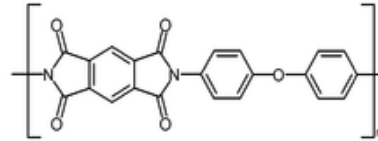
$$D = \frac{Eh^3}{12(1-\nu^2)}$$

elastic modulus

thickness

Typical stress - strain curves





Kapton®



- **Imide-based polymer**

- Imide: 2 acyl groups bonded to nitrogen

- **Thermoplastic**

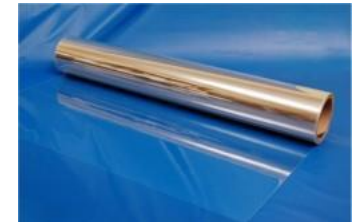
- Available as a foil
- Spinnable as an uncured resin
- Can be photosensitive



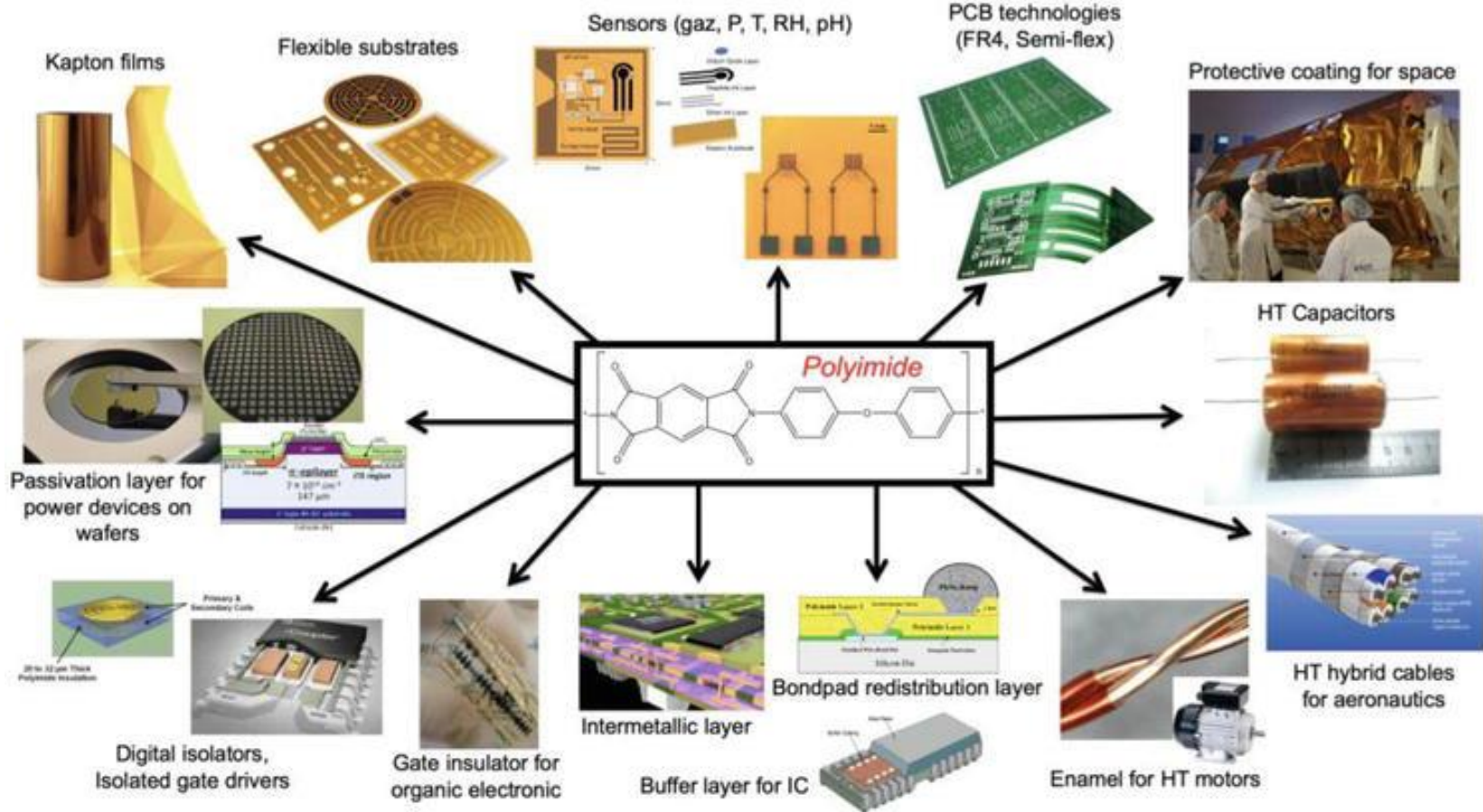
- **Good thermal and mechanical stability**

- Young's modulus: ~2.5 GPa
- CTE: 20 – 60 ppm/°C

- High resistance to solvents and weak acids

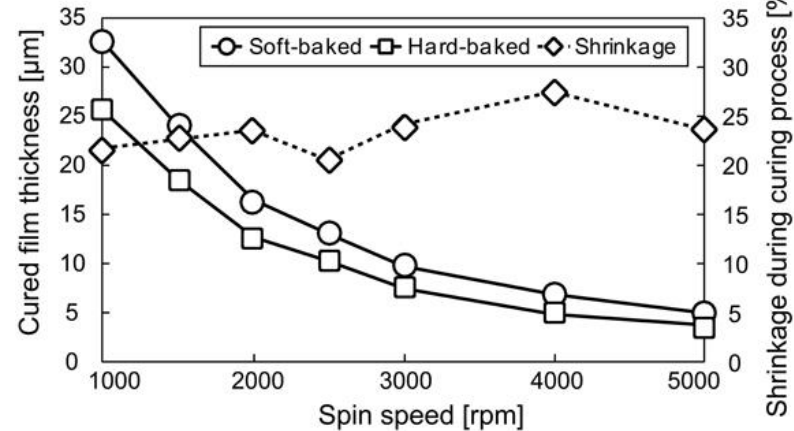
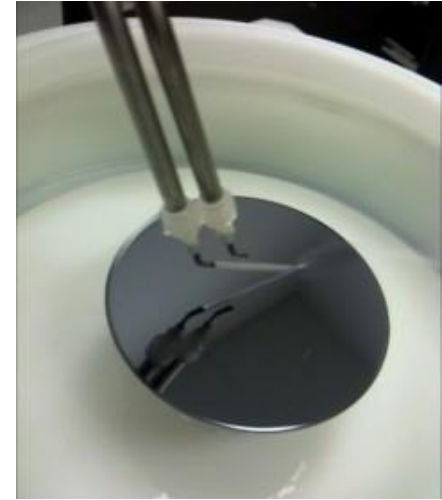
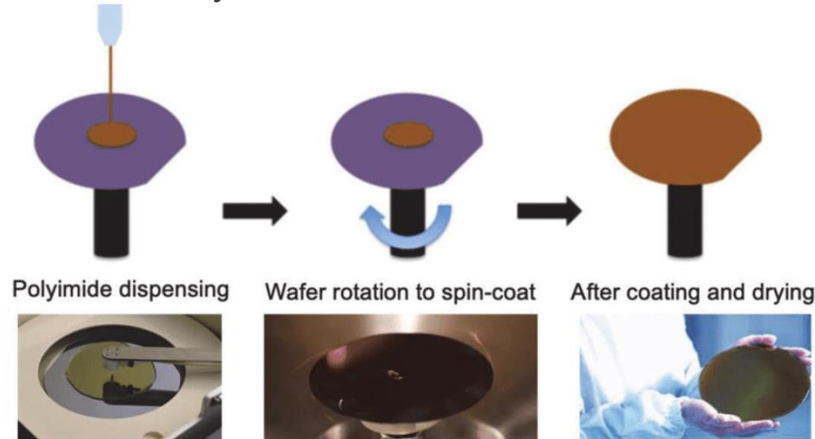


Polyimide applications

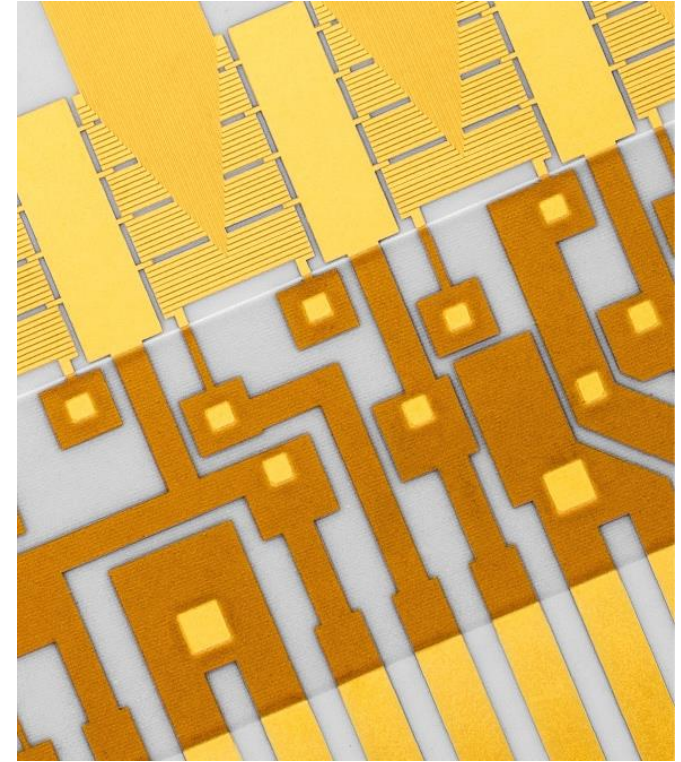
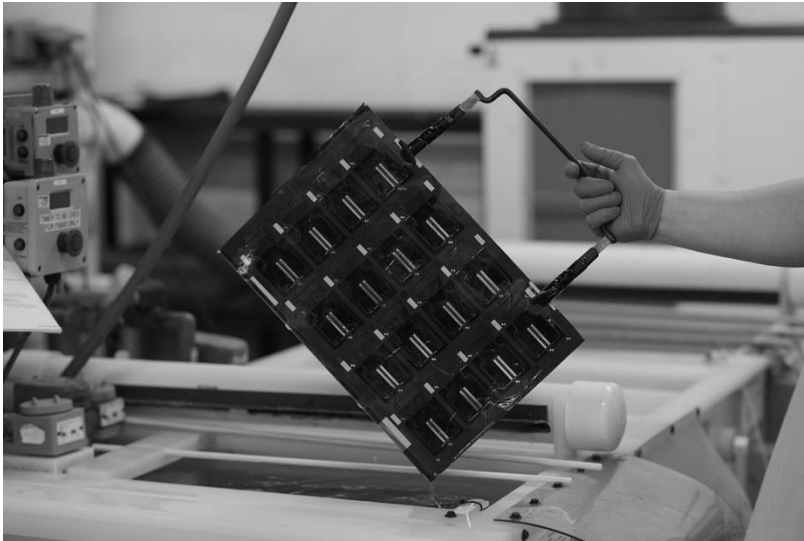


Forming and processing a thin polyimide film

1. Clean the rigid carrier e.g. a silicon or glass slide
 - Apply adhesion promoter (optional)
2. Spin-coat liquid polyamic acid (precursor to polyimide)
 - Spin speed \rightarrow thickness (1 – 20 μm typically)
 - Ramps \rightarrow uniformity and edge beads
3. Soft bake (remove solvent)
4. Hard bake (aka curing, imidisation: *polyamic acid* \rightarrow *polyimide*)
 - Up to 300-400°C, often in *N* atmosphere
 - Robust, thermally stable film



- 5. Photolithography (positive or negative photoresist)
- 6. Patterning typically by **oxygen plasma RIE**
 - Photoresist as a mask: ~1:1 etch ratio
- 7. Photoresist strip (oxygen plasma (careful) or solvent)



Thin-film metallization on polyimide



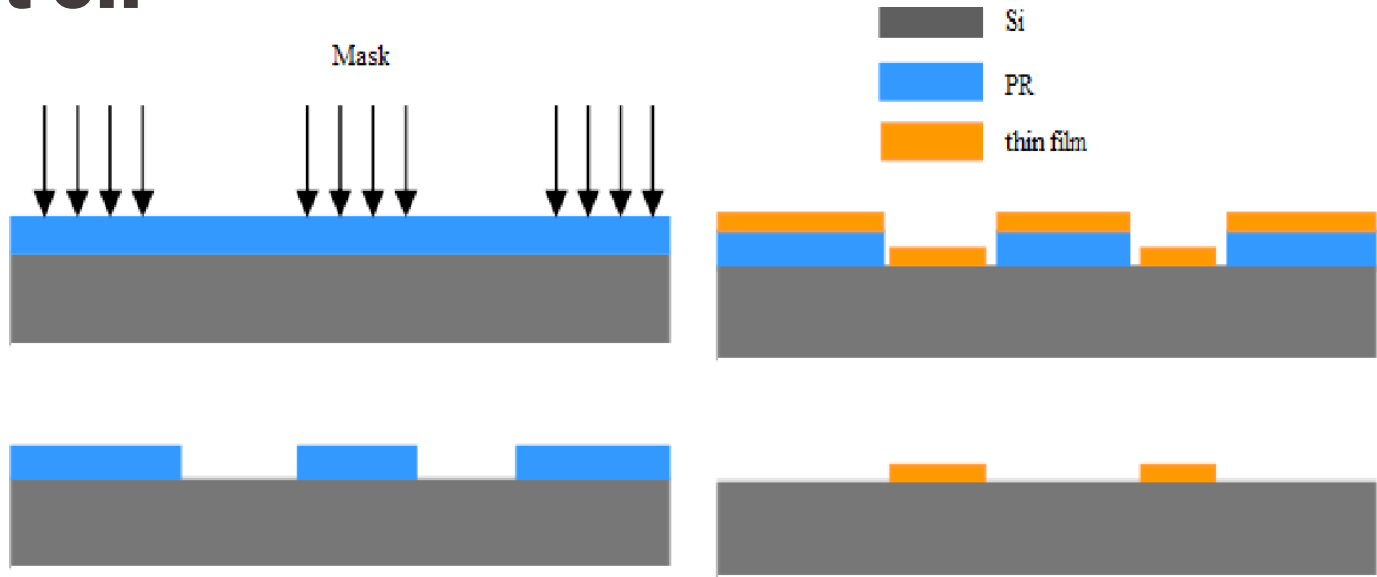
1. Spin-coat the substrate polymer (PI)
Material and thickness
2. Evaporate metal
Material and thickness
3. Photolithography
Mask preparation, photoresist spin-coating & baking
Curing, development
4. Metal etching
Dry or wet process
5. Photoresist strip
Wet process
6. Substrate release
Wet or mechanical process



Example materials and processes:

- Aluminium sacrificial layer, etch-release process by anodic dissolution:
 - Al **sacrificial layer** under polyimide devices
 - Al biased as **anode (2-20V)** oxidizes to Al^{3+} and dissolves ($\text{Al} \rightarrow \text{Al}^{3+} + 3\text{e}^-$)
 - Al dissolves from edges/access windows; device lifts-off from carrier wafer
- SiO_2 sacrificial layer, etch-release process by wet HF:
 - High selectivity (PI unattacked)

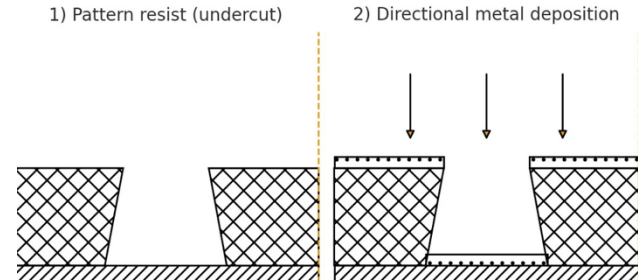
→ Many release processes possible, but the device stack typically restricts the choice to very few options



DOI:[10.51847/7tmarkoorg](https://doi.org/10.51847/7tmarkoorg)

Figure 1. Lift-off process

- Avoids etching step (no need to stack compatibility check)
- Requires careful photoresist profiling and ~directional (non-conformal) thin-film deposition



Thin-film Pt on flex PI: general process flow

1. Polyimide spincoating on Si wafer / release layer + curing



2. Ti/Pt/Ti sputtering



3. PR coating and patterning (photolithography)



4. Ti/Pt/Ti etching (IBE)



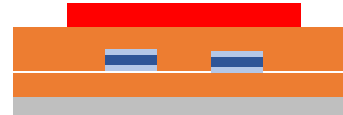
5. PR stripping



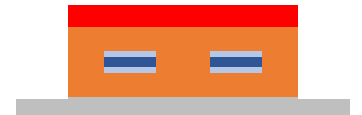
6. Polyimide spincoating + curing



7. PR coating and patterning (photolithography)



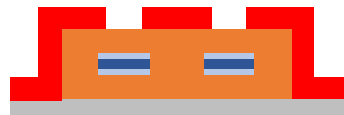
8. Polyimide etching (DRIE)



9. PR stripping



10. PR coating and patterning (photolithography)



11. Polyimide etching (DRIE) + Ti etching (IBE)



12. PR stripping



Si

Polyimide

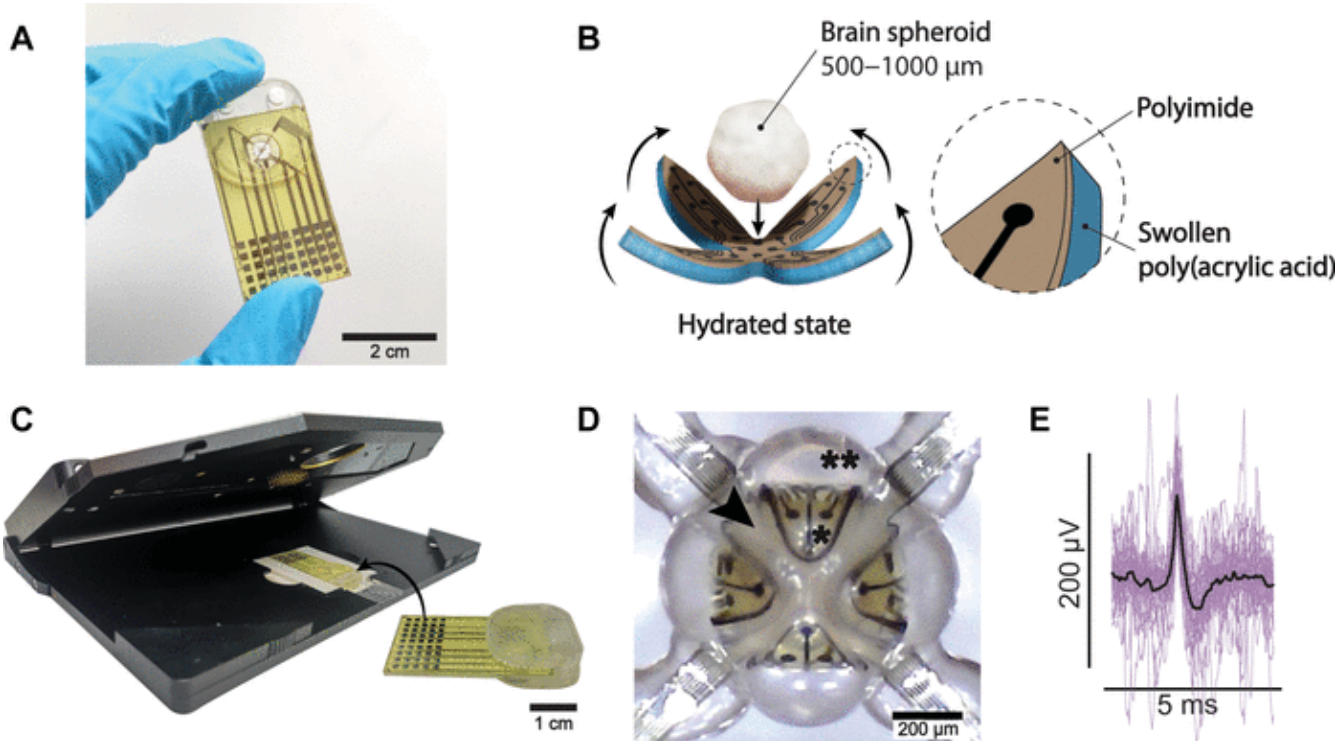
Ti

Pt

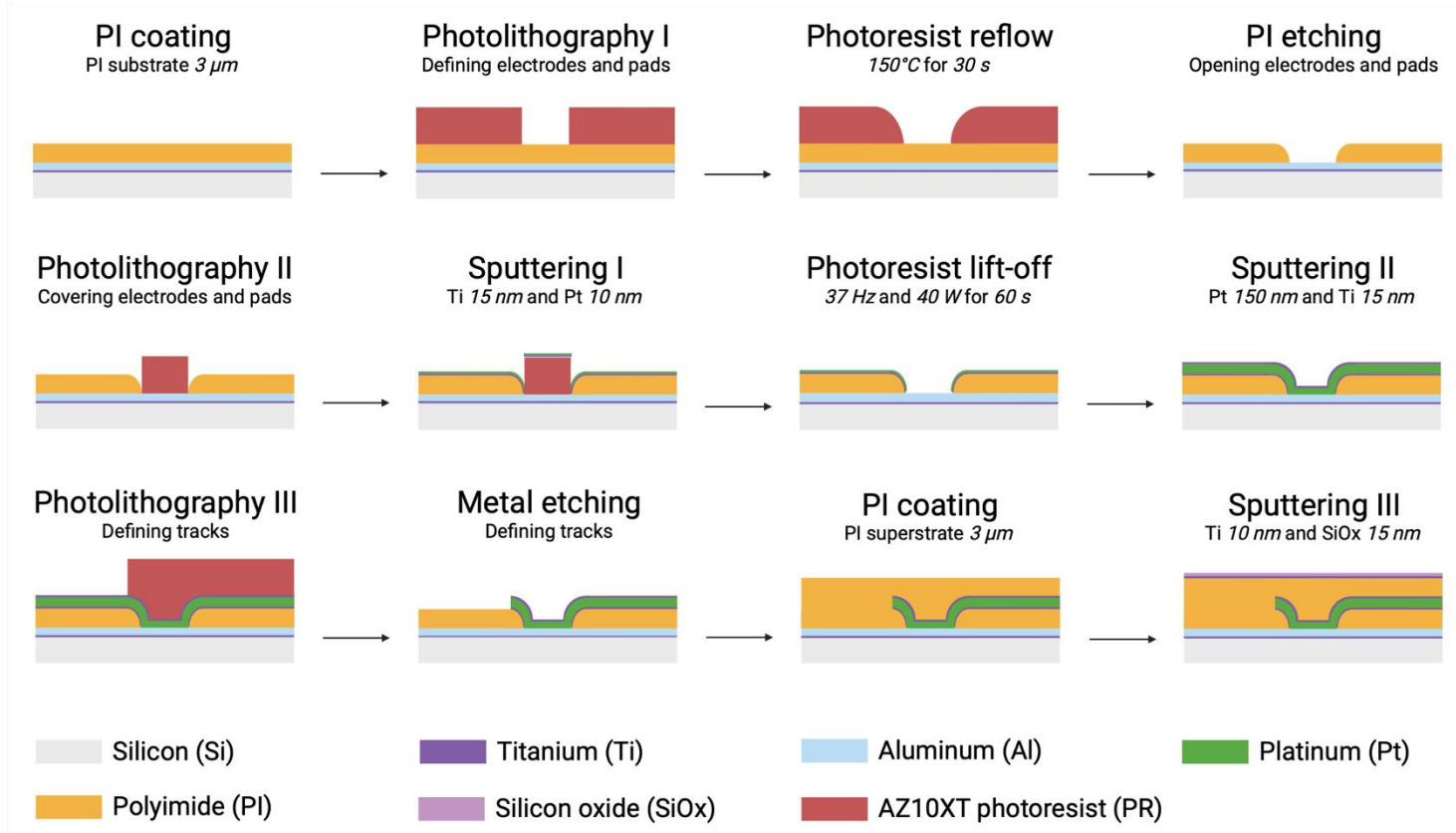
PR

Case study: the e-flower

- You want to graft a hydrogel to a polyimide-based device to actuate it. How can you design a process flow?

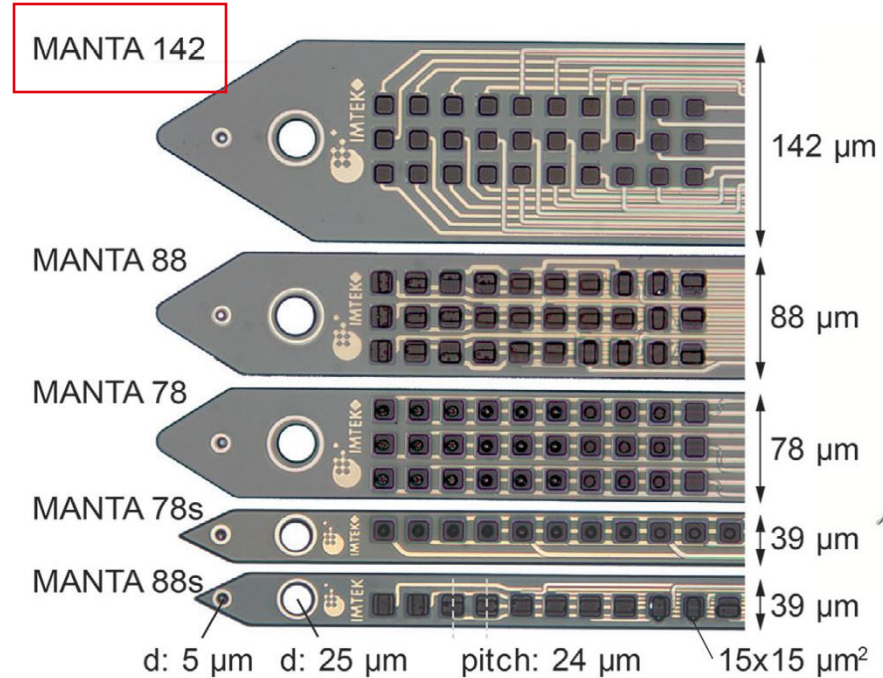


Example process flow: the e-flower PI device

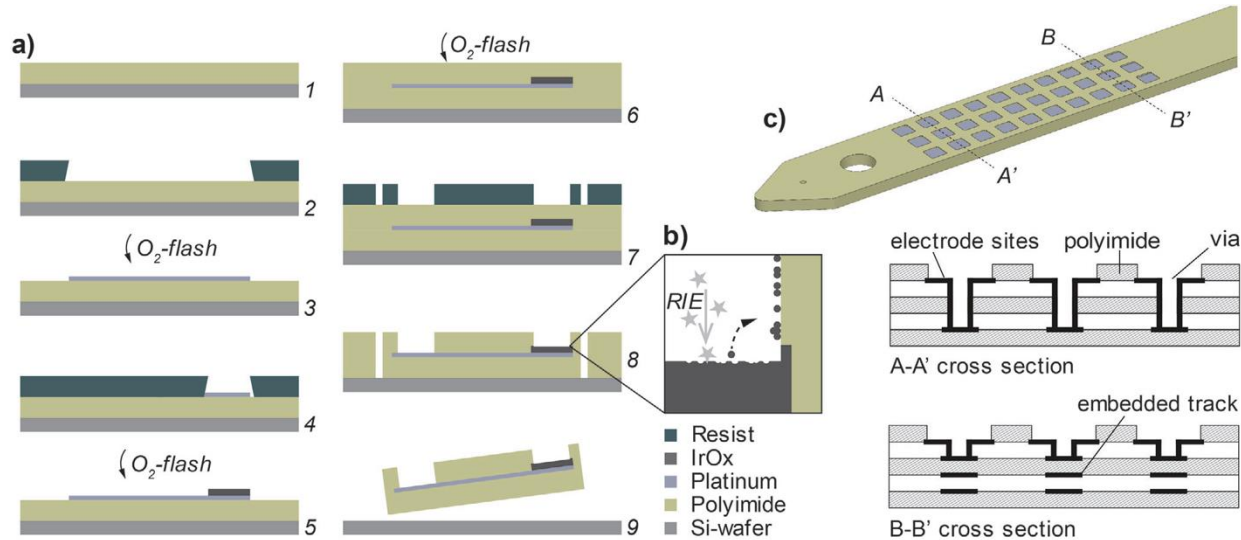


Polyimide based shank with high density electrodes

Analyse the photos.
Propose the list of materials.
Prepare cross-sections.
Propose a process flow.



Polyimide based shank with high density electrodes



Polyimide based shank with high density electrodes

MANTA probes were fabricated by advancing **standard PI fabrication** protocols to a multilayer design, comprising ultimately **5 PI and 7 metallization layers** in a probe of **10 μm thickness**.

First a **2 μm thin layer of PI** (U-Varnish S, UBE corporation) was spincoated onto a carrier wafer and cured at 450°C under nitrogen atmosphere (YES- 450PB8-4PB/E, Yield Engineering Systems Inc.).

A **lift-off-resist** (AZ5214E, MicroChemicals GmbH) was subsequently used to pattern the first **Pt layer** (100 nm, static evaporation, Univex 500, Leybold).

Prior to the **metal deposition**, the PI-surface was activated in an O₂-plasma (30 s at 100 W, STS-RIE) to ensure stable adhesion between the layers.

After another O₂-plasma treatment, this metal layer was insulated with a **second PI layer** (2 μm), which was then partially opened by reactive ion etching using an O₂-plasma (100 W, STS-RIE) and a resist mask (AZ9260, MicroChemicals GmbH) to define the **first set of vias**.

A **second Pt-layer** was afterward deposited (following again an O₂-plasma treatment and using the same parameters as previously described) to define the tracks and electrodes in the second metallization plane.

The **electrode sites** were additionally coated with a sputtered iridium oxide (**SIROF**) layer (800 nm, 100 W, 15 sccm O₂, Univex 500, Leybold) using again a **lift-off resist** to define the electrode geometry.

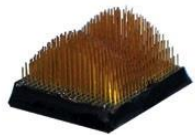
The **same process steps** (O₂-plasma, Pt + SIROF-deposition, and PI-insulation) **were repeated twice** to build up a total stack of **5 PI layers with 4 Pt-metallization planes** and three SIROF layers.

The topmost PI-layer was finally patterned using RIE to realize simultaneously the electrode openings above the SIROF sites, to open the Pt-pads for solder interconnection at the backend of the probe, as well as to define the overall outline of the probe.

For further use and characterization, probes were individually peeled off from the carrier wafer.

Hard interfaces

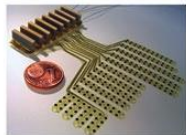
Tungsten microwire array:
~200 GPa



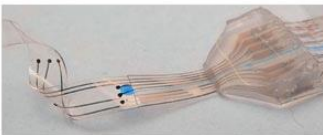
Silicon Utah array:
~150 GPa



Thin polyimide array:
~5 GPa



Electronic dura:
~1 MPa



E

100 GPa

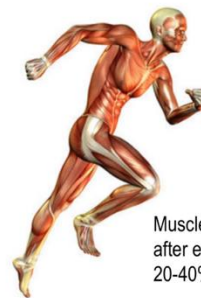
1 GPa

1 MPa

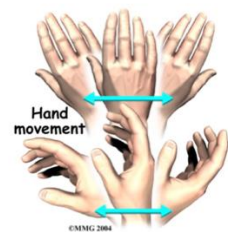
1 kPa

Soft interfaces

Dynamic interfaces

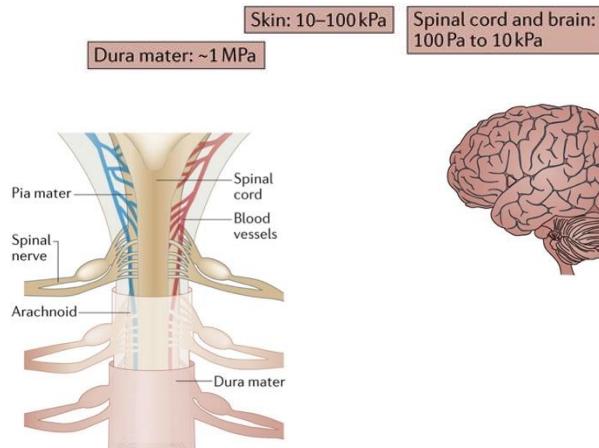
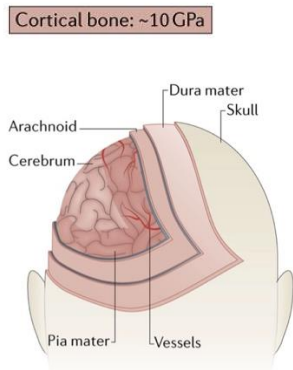


Muscle expansion
after exercise:
20-40% vol.



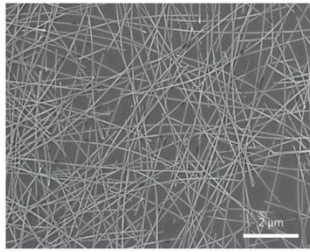
Multi-axial movements

■ Biological tissue
□ Neural implants

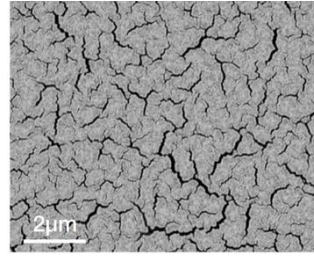


Stevens Institute of Technology, NJ, USA

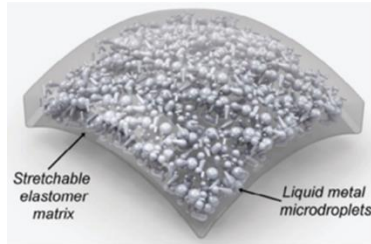
Intrinsic stretchability



Composite of AgNW and elastomer [1]

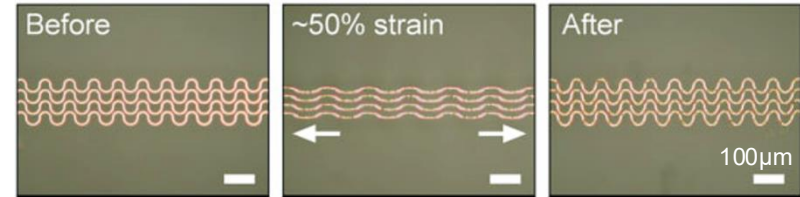


Micro-cracked gold on PDMS [2]

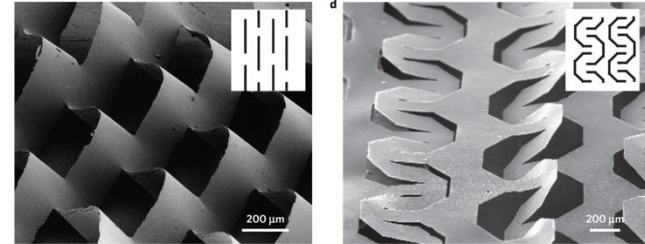


Liquid metal [3]

Stretchability by design



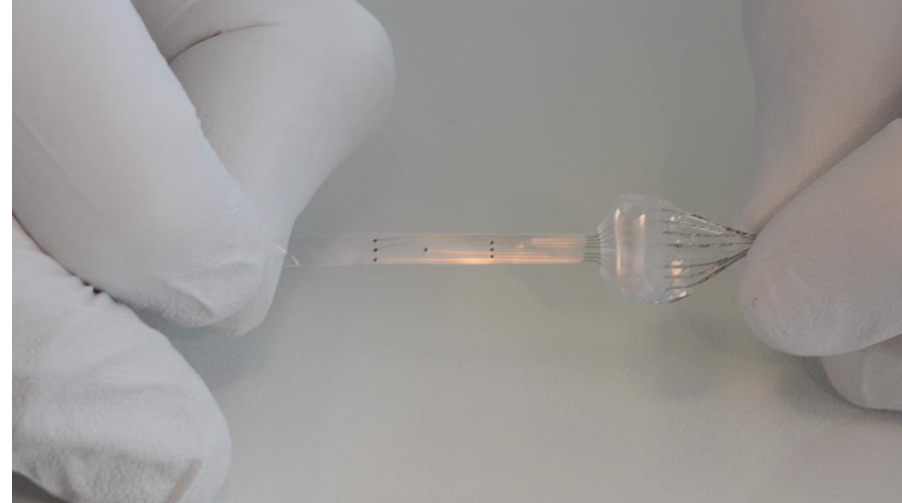
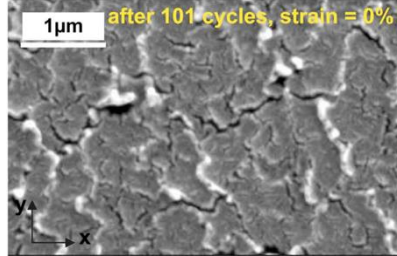
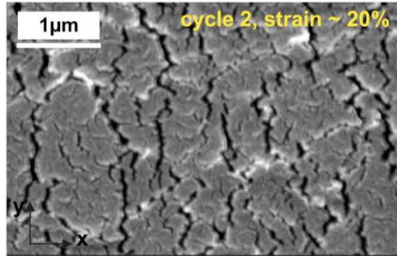
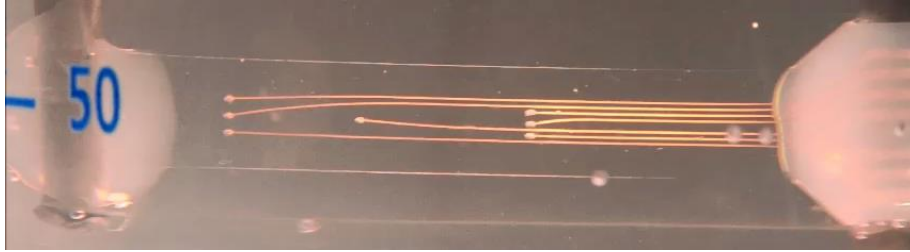
Serpentines [4]



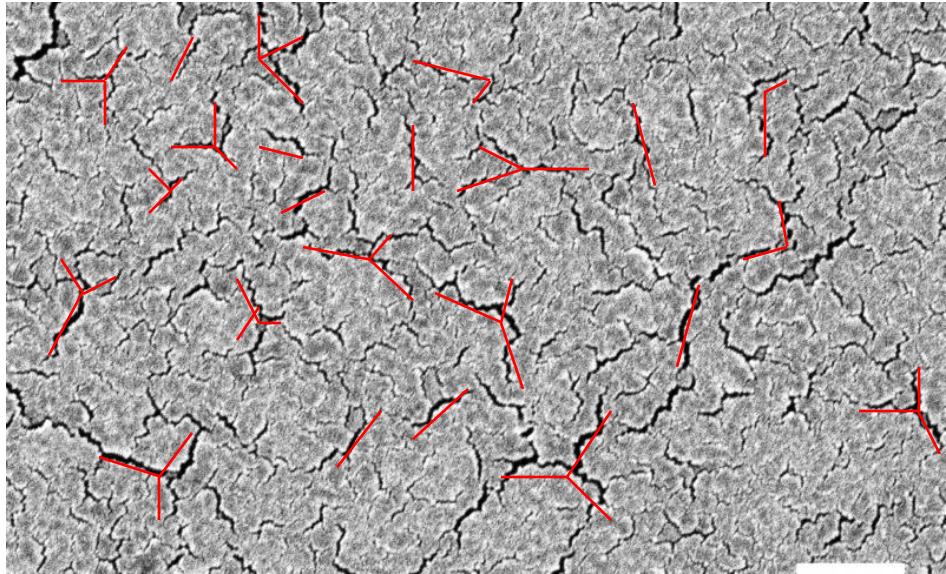
Periodic cuts (kirigami) [5]

- [1] J. Liang et al. (2013), [2] I. R. Mineev et al. (2015), [3] N. Matsuhisa et al. (2019),
[4] D. S. Gray et al. (2004), [5] T. C. Shyu et al. (2015)

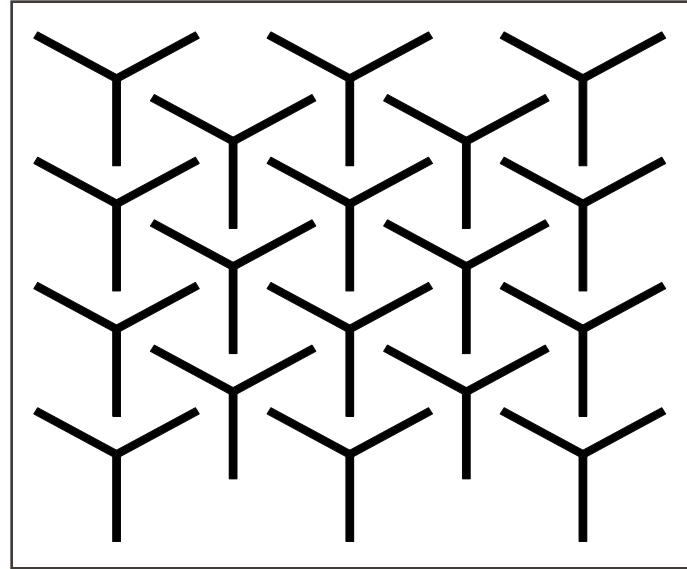
Engineering reversible deformation in thin-film conductors



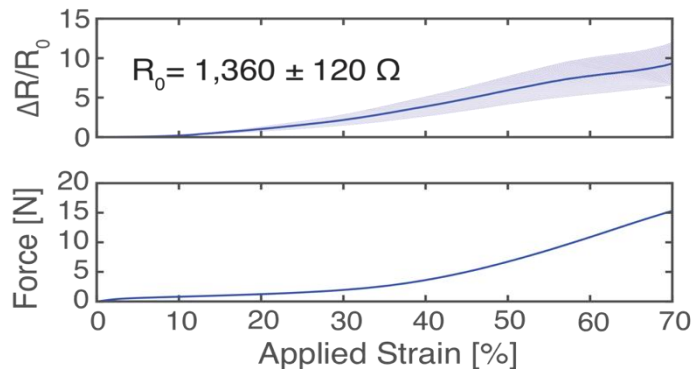
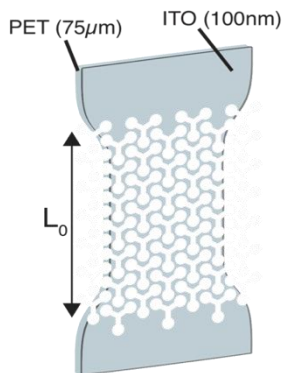
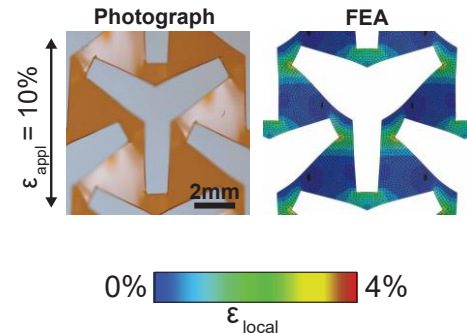
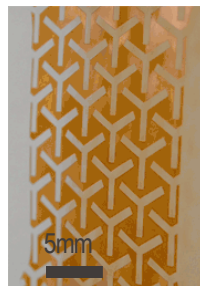
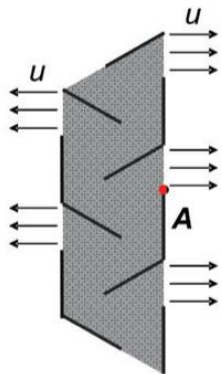
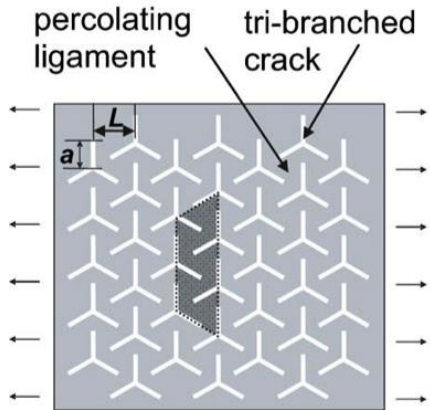
Naturally occurring phenomenon



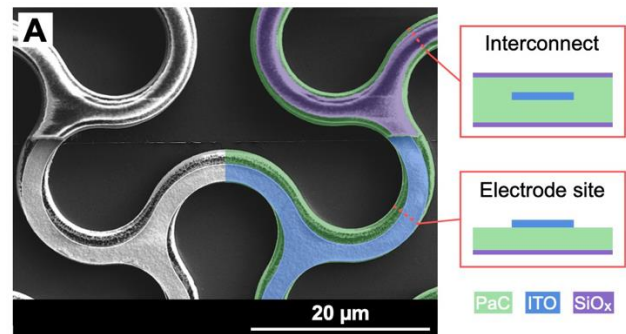
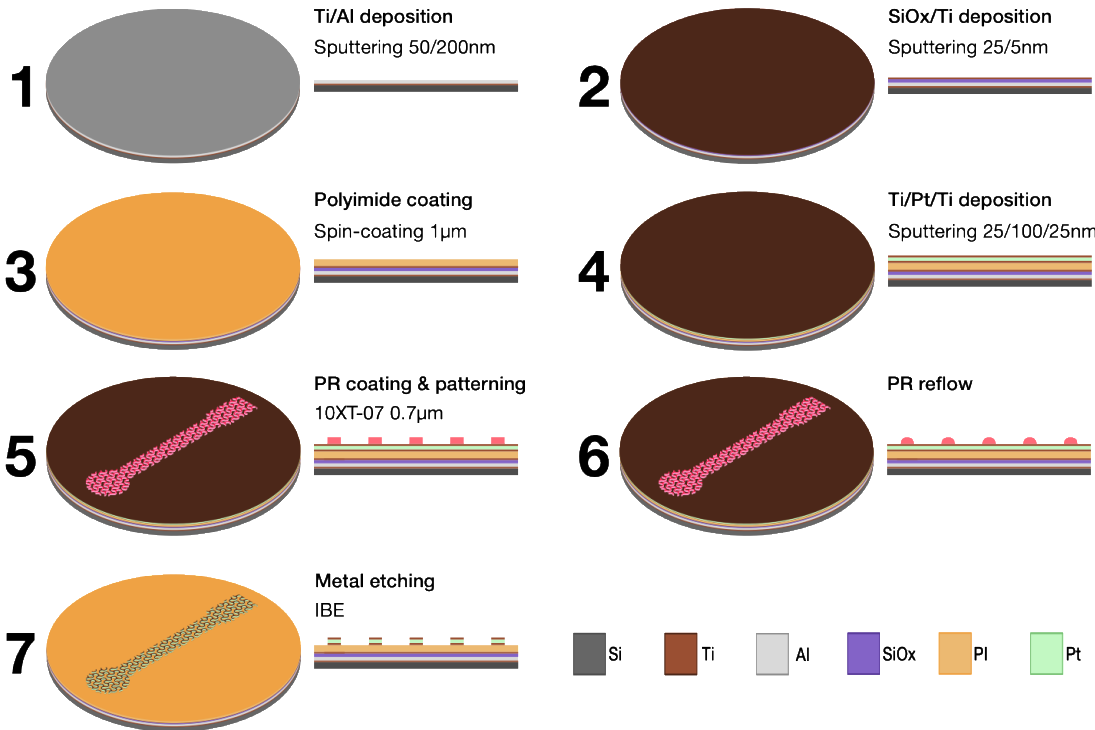
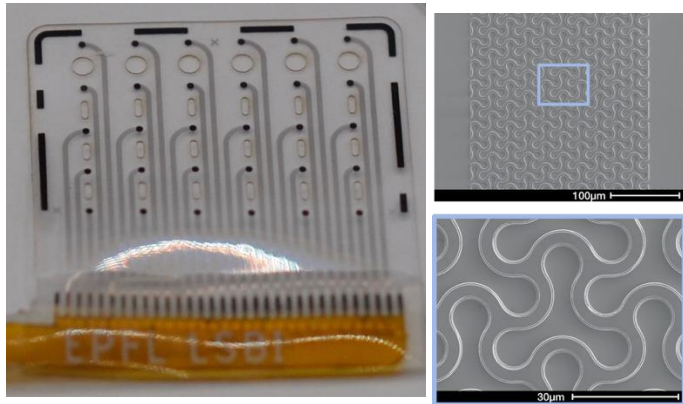
Microstructured patterns



Kirigami approach

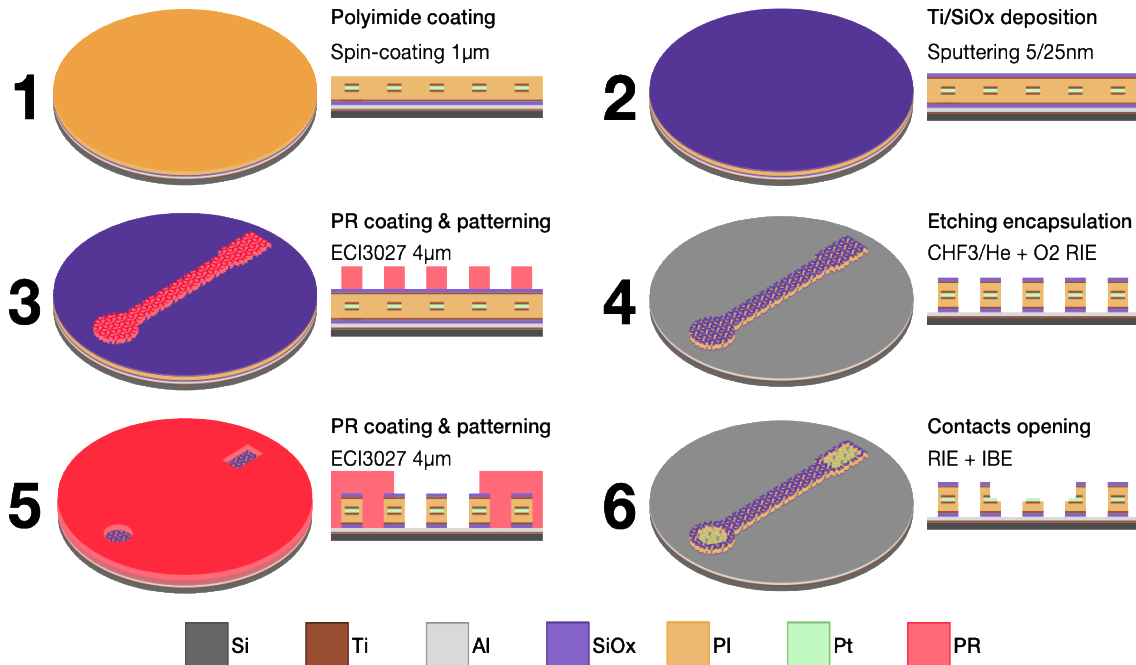
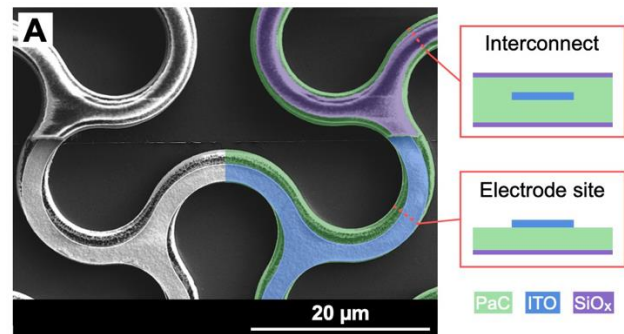
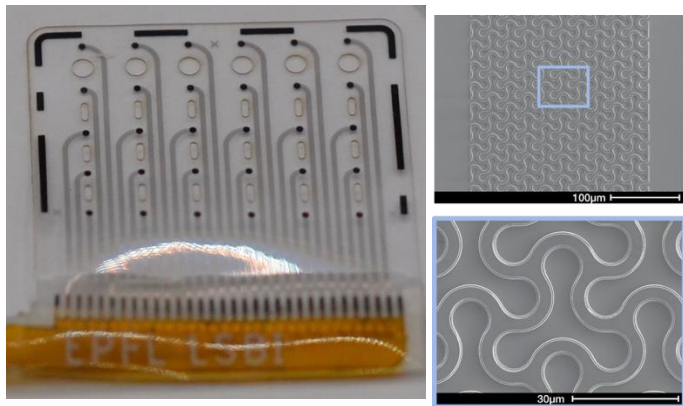


Process flow: Kirigami-inspired neurotechnology



Process flow: Kirigami-inspired neurotechnology

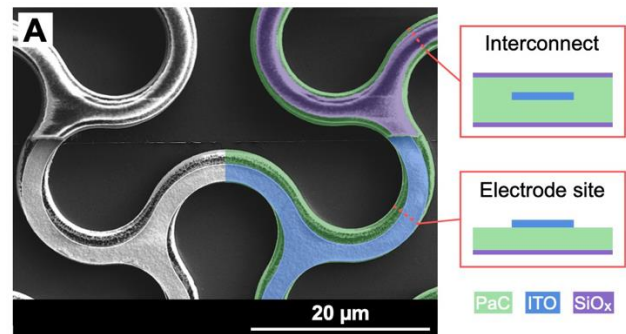
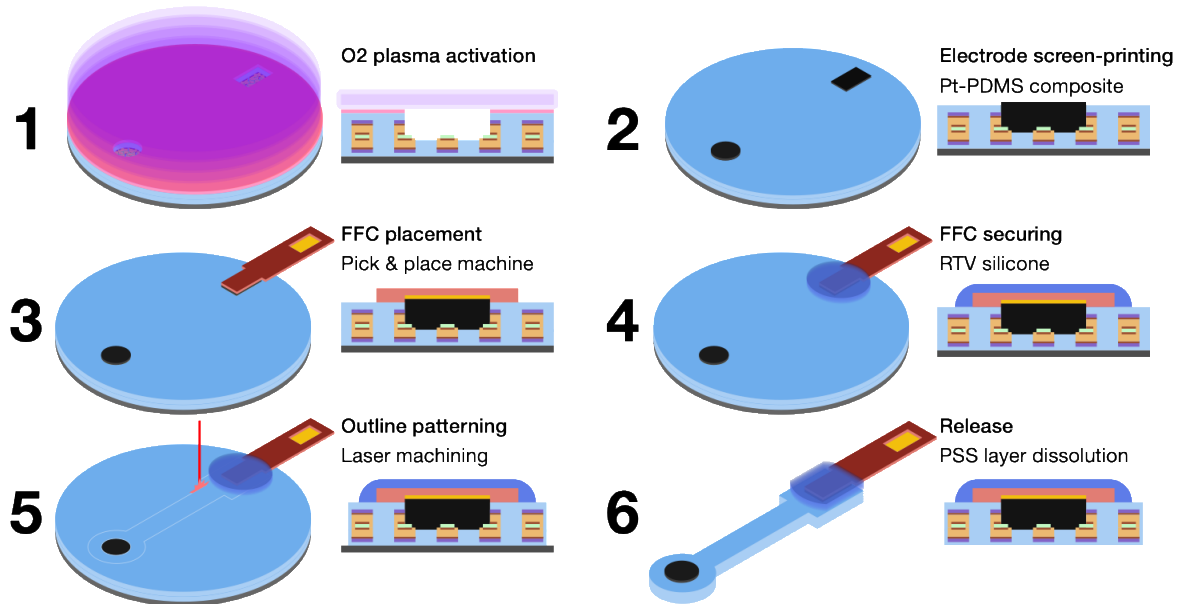
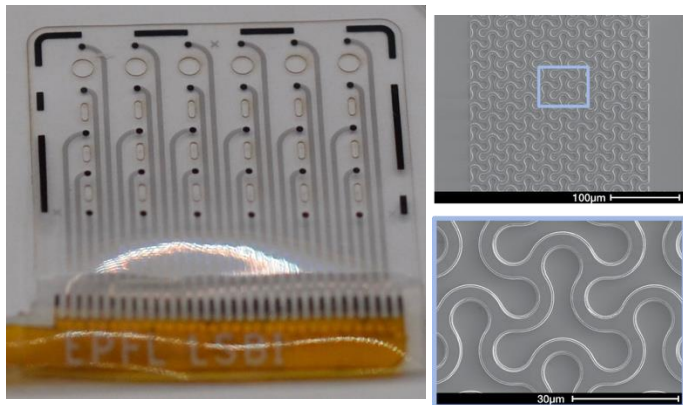
(numbering should continue from previous slide)



Process flow: Kirigami-inspired neurotechnology

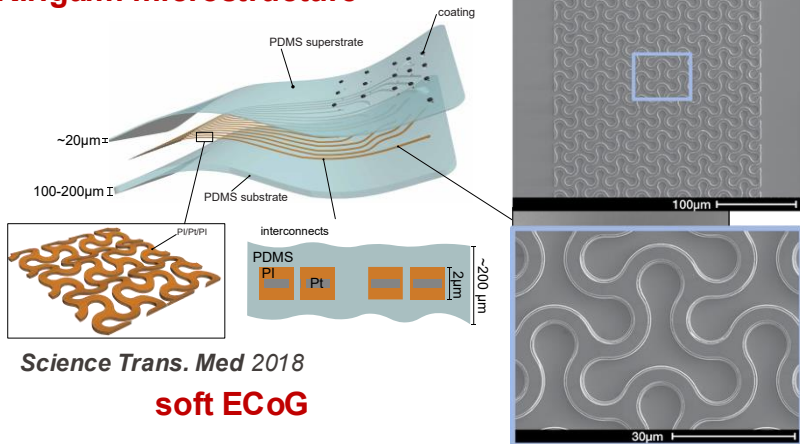
(numbering should continue from previous slide)

Some skipped steps: silicone encapsulation bonding to PI



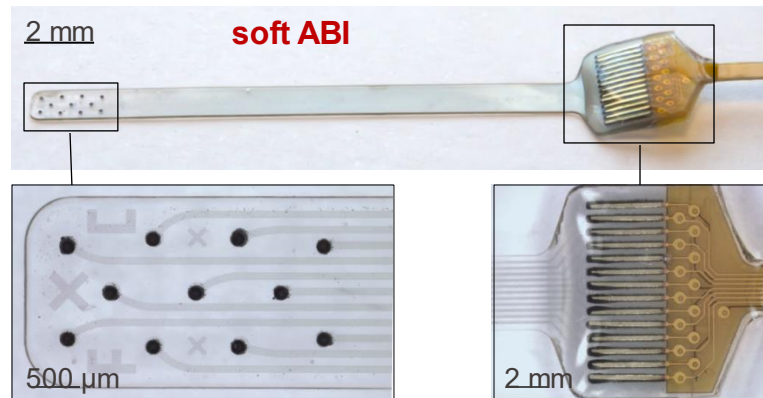
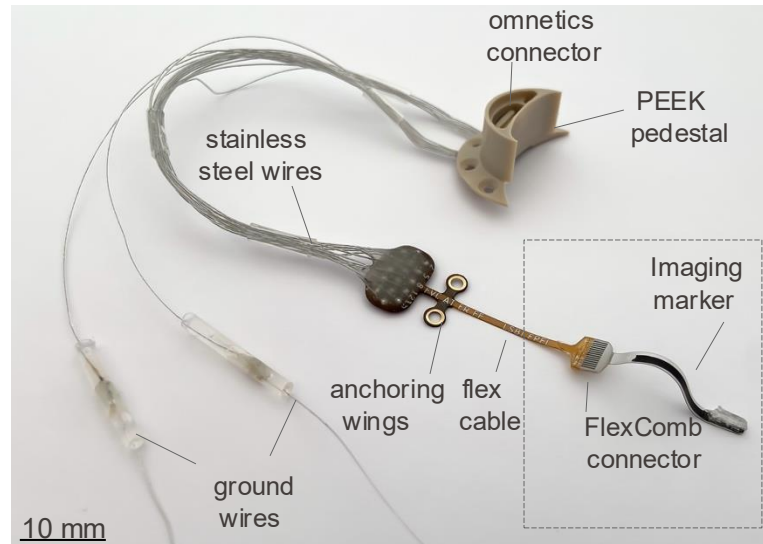
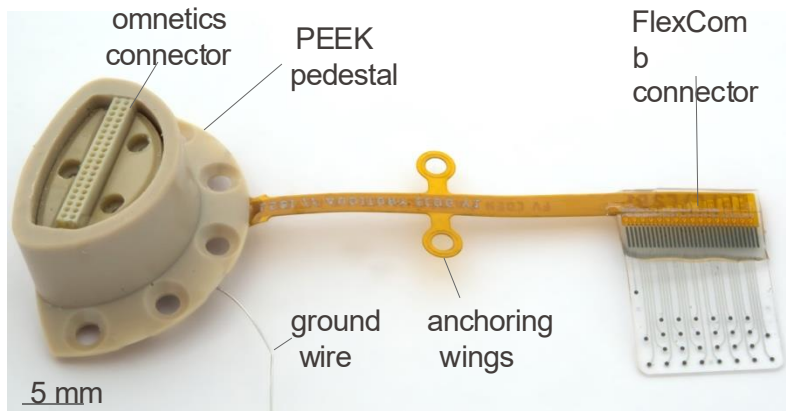
→ Compliant implants

Kirigami microstructure



Science Trans. Med 2018

soft ECoG



- Silicon is a material of choice for microfabrication
- We can borrow the same technological framework and apply it to processing on polymers. Silicon acts as carrier for processing only.
- We leverage microfabrication to manufacture flexible devices (based on thin polymer foils, typified by polyimide)
- We can apply microstructuring (Kirigami) to further introduce elasticity
- We have shown applications in neuroelectronic interfaces, but many other domains benefit from compliant microtechnology

▪